



# Pseudo SRAM 32Mb and 64Mb

ISSI is now ramping up production of the 32Mb and 64Mb PSRAMs, the latest additions to our SRAM portfolio. 32Mb and 64Mb Pseudo SRAMs provide a cost effective solution to a standard Ultra-Low Power SRAM socket.

## Key Features for the 64Mb Pseudo SRAM

	IS66WVx4M16
Density	64Mb (4Mx16)
Technology	DRAM Cell
Standby Current (Typical)*	85µA
Operating Current (Typical)*	17mA
Packaging	BGA, KGD
Options	1.8V/3.3V Async/Page, CRAM 1.5/2.0
Temperature Support	0°C to +70°C Commercial -40°C to +85°C Industrial
Status	Production

\*Typical data for the 1.8V Async/Page option at 25°C.



## ► Applications

- Mobile
- Industrial
- Automotive
- Telecom/Networking

## Options Table

Den	Org	Part No.	Vcc	Speed (ns)	Pkg (#Pins)	Comment
32M	2Mx16	IS66WVC2M16ALL	1.8V	70	VFPGA(54)	Lead-free, CRAM 1.5
	2Mx16	IS66WVD2M16ALL	1.8V	70	VFPGA(54)	Lead-free, CRAM 2.0
	2Mx16	IS66WVE2M16ALL	1.8V	70	TFPGA(48)	Lead-free, Asynch/Page
	2Mx16	IS66WVE2M16BLL	3.3V	70	TFPGA(48)	Lead-free, Asynch/Page
64M	4Mx16	IS66WVC4M16ALL	1.8V	70	VFPGA(54)	Lead-free, CRAM 1.5
	4Mx16	IS66WVD4M16ALL	1.8V	70	VFPGA(54)	Lead-free, CRAM 2.0
	4Mx16	IS66WVE4M16ALL	1.8V	70	TFPGA(48)	Lead-free, Asynch/Page
	4Mx16	IS66WVE4M16BLL	3.3V	70	TFPGA(48)	Lead-free, Asynch/Page

Pseudo SRAMs are ideal for cost-sensitive applications where higher standby current is acceptable. PSRAMs have certain timing restrictions when compared to a regular SRAM.

For more information, please refer to ISSI's website for complete Pseudo SRAM datasheets.